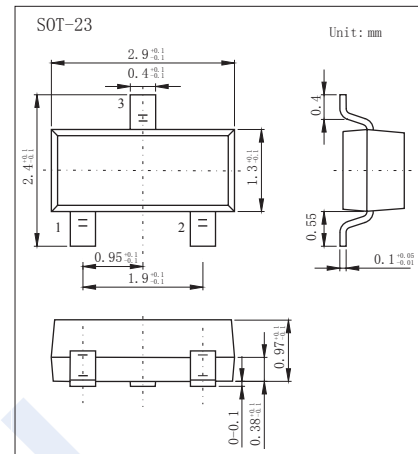
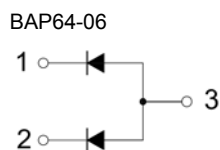
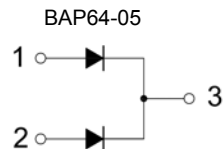
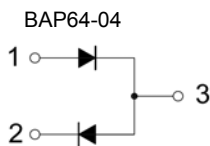


## PIN Diodes

## BAP64-04/05/06 (KAP64-04/05/06)

### ■ Features

- High voltage, current controlled
- RF resistor for RF attenuators and switches
- Low diode capacitance
- Low diode forward resistance
- Low series inductance
- For applications up to 3 GHz.



### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Continuous Reverse Voltage	$V_R$	175	V
Continuous Forward Current	$I_F$	100	mA
Power Dissipation @ $T_s = 90^\circ\text{C}$	$P_D$	250	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	500	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature range	$T_{stg}$	-65 to 150	

## PIN Diodes

## BAP64-04/05/06 (KAP64-04/05/06)

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 50 mA			1.1	V
Reverse voltage leakage current	I <sub>R</sub>	V <sub>R</sub> =175V			10	uA
		V <sub>R</sub> =20 V			1	
Diode forward resistance (Note.1)	r <sub>D</sub>	I <sub>F</sub> = 0.5 mA , f = 100 MHz			40	Ω
		I <sub>F</sub> = 1 mA , f = 100 MHz			20	
		I <sub>F</sub> = 10 mA , f = 100 MHz			3.8	
		I <sub>F</sub> = 100 mA , f = 100 MHz			1.35	
Diode capacitance	C <sub>d</sub>	V <sub>R</sub> = 0 V, f= 1 MHz		0.52		pF
		V <sub>R</sub> = 1 V, f= 1 MHz			0.5	
		V <sub>R</sub> = 20 V, f= 1 MHz			0.35	
Series inductance	L <sub>s</sub>	I <sub>F</sub> =10mA, f=100MHz		1.4		nH
Charge carrier life time	T <sub>L</sub>	when switched from I <sub>F</sub> = 10 mA to I <sub>R</sub> = 6mA; R <sub>L</sub> = 100 Ω; measured at I <sub>R</sub> = 3 mA		1.55		us

Note.1: Guaranteed on AQL basis: inspection level S4, AQL 1.0.

## ■ Marking

NO	BAP64-04	BAP64-05	BAP64-06
Marking	4K	5K	6K

### PIN Diodes

### BAP64-04/05/06 (KAP64-04/05/06)

■ Typical Characteristics

